1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-0049-B

2. Structure :

2-1. Type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold.

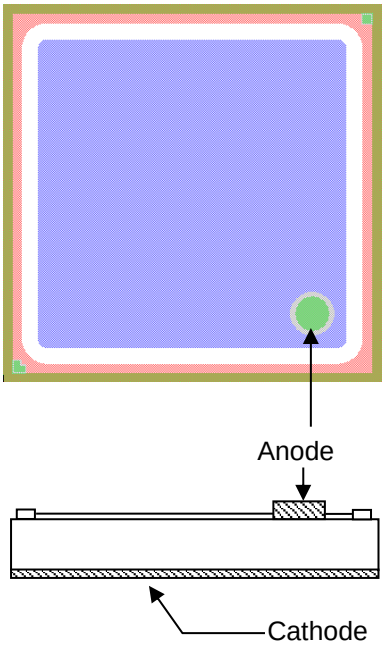
3. Size :

3-1. Chip size : 48.4 mils x 48.4 mils (1.230 mm x 1.230 mm).
3-2. Chip thickness : 15.75 ± 1.5 mils (0.400 ± 0.038 mm).
3-3. Active area : 39.4 mils x 39.4 mils (1.000 mm x 1.000 mm).
3-4. Bonding pad (Anode) : 5.5 mils x 5.5 mils (0.140 mm x 0.140 mm).
3-5. Pattern drawing : Refer to the attached drawing

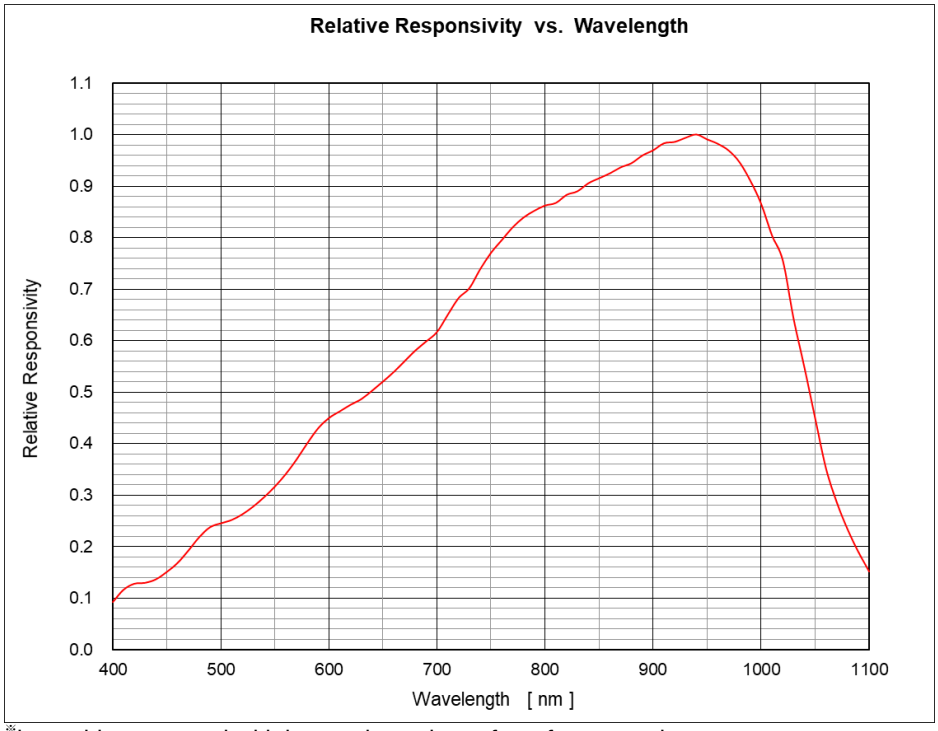
4. Electro-optical characteristics (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark Current	I_D	V_R=10V Ee=0mW/cm^2			5	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=10uA Ee=0mW/cm^2	60			V
Open circuit voltage	Voc	T=2856K Ee=5mW/cm^2		350		mV
Short circuit Current	Isc	T=2856K Ee=5mW/cm^2		7		μA
Total Capacitance	C_t	V_R =5V Ee=0mW/cm^2 f=1MHz		12.5		pF
Responsivity	S	VR=5V λp=850nm		0.55		A / W

※Based on 100% probing



5. Relative spectral responsivity



※bare chip measured with integrating sphere, for reference only.